

1. Scope :

This specification applies to NIP silicon photodiode chips,
Device No. PD-2065B

2. Structure :

- 2-1. Planar type : NIP diode.
- 2-2. Electrodes :
 Top side (Cathode) : Aluminum alloy .
 Back side (Anode) : Gold alloy.

3. Size :

- 3-1. Chip size : 64 mils x 64 mils (1.63 mm x 1.63 mm).
- 3-2. Chip thickness : 12 ± 1.5 mils (0.305 ± 0.038 mm).
- 3-3. Active area : 56.7 mil x 56.7 mils (1.44 mm x 1.44 mm).
- 3-4. Bonding pad (Cathode) : 10 mils x 10 mils (0.255 mm x 0.255 mm).
- 3-5. Pattern drawing : Refer to the attached drawing

4. Electro-optical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
*Reverse dark Current	I_D	$V_R=10V$ $E_e=0mW/cm^2$			10	nA
*Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu A$ $E_e=0mW/cm^2$	60			V
Open circuit voltage	V_{oc}	$T=2856K$ $E_e=5mW/cm^2$		390		mV
Short circuit Current	I_{sc}	$T=2856K$ $E_e=5mW/cm^2$		18		μA
Reverse light current	I_L	$V_R =5V$ $T=2856K$ $E_e=5mW/cm^2$		18		μA
Total Capacitance	C_t	$V_R =5V$ $E_e=0mW/cm^2$ $f=1MHz$		9		pF
Turn-on/ Turn-off time	ton/toff	$V_R=5V$ $R_L=50\Omega$ $\lambda =850nm$		50/50		nS

*Based on 100% probing

